CM300DY-24NF

HIGH POWER SWITCHING USE

CM300DY-24NF

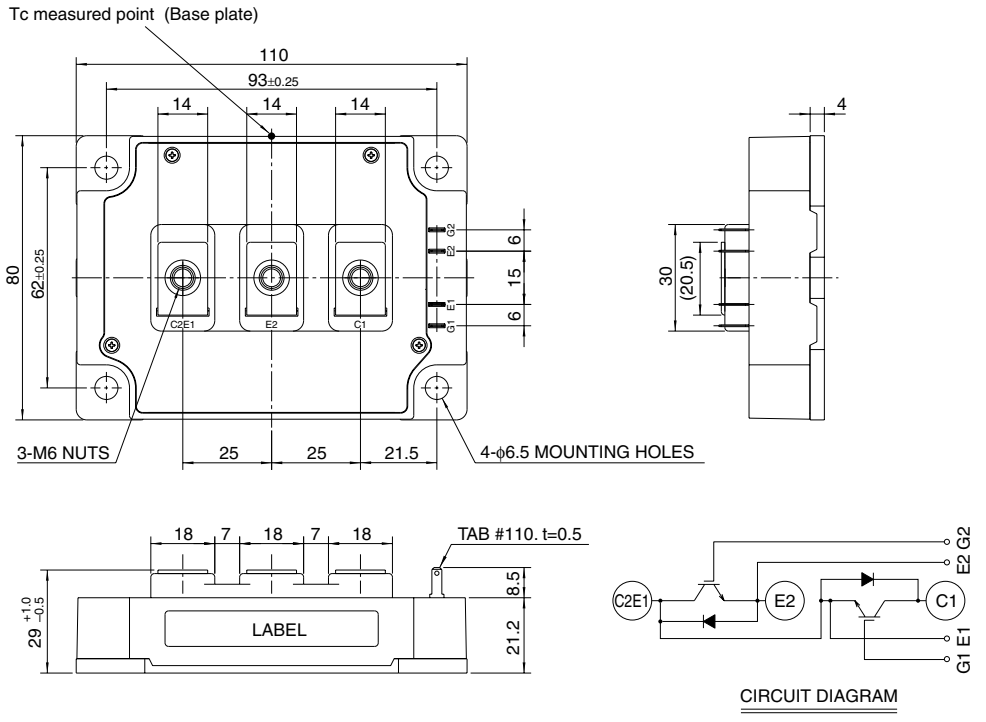
- I_C 300A
- V_{CES} 1200V
- Insulated Type
- 2-elements in a pack

APPLICATION

General purpose inverters & Servo controls, etc

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



MITSUBISHI ELECTRIC

MAXIMUM RATINGS (Tj = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Collector-emitter voltage	G-E Short	1200	V
V_{GES}	Gate-emitter voltage	C-E Short	±20	V
I_C	Collector current	DC, T_C' = 111°C*3	300	A
I_{CM}		Pulse (Note 2)	600	A
I_E (Note 1)	Emitter current		300	A
I_{EM} (Note 1)		Pulse (Note 2)	600	A
P_C (Note 3)	Maximum collector dissipation	T_C = 25°C	1130	W
T_j	Junction temperature		–40 ~ +150	°C
T_{stg}	Storage temperature		–40 ~ +125	°C
V_{iso}	Isolation voltage	Main Terminal to base plate, AC 1 min.	2500	V
—	Torque strength	Main Terminal M6	3.5 ~ 4.5	N • m
—		Mounting holes M6	3.5 ~ 4.5	N • m
—	Weight	Typical value	580	g

ELECTRICAL CHARACTERISTICS (Tj = 25°C)

Symbol	Parameter	Test conditions		Limits			Unit
				Min.	Typ.	Max.	
I_{CES}	Collector cutoff current	V_{CE} = V_{CES}, V_{GE} = 0V		—	—	1	mA
$V_{GE(th)}$	Gate-emitter threshold voltage	I_C = 30mA, V_{CE} = 10V		6	7	8	V
I_{GES}	Gate leakage current	V_{GE} = V_{GES}, V_{CE} = 0V		—	—	0.5	μA
$V_{CE(sat)}$	Collector-emitter saturation voltage	T_j = 25°C	I_C = 300A, V_{GE} = 15V	—	1.8	2.5	V
		T_j = 125°C		—	2.0	—	
C_{ies}	Input capacitance	V_{CE} = 10V, V_{GE} = 0V		—	—	70	nF
C_{oes}	Output capacitance			—	—	6	nF
C_{res}	Reverse transfer capacitance			—	—	1.4	nF
Q_G	Total gate charge	V_{CC} = 600V, I_C = 300A, V_{GE} = 15V		—	2000	—	nC
$t_{d(on)}$	Turn-on delay time	V_{CC} = 600V, I_C = 300A, V_{GE1} = V_{GE2} = 15V, R_G = 1Ω, Inductive load switching operation, I_E = 300A		—	—	500	ns
t_r	Turn-on rise time			—	—	150	ns
$t_{d(off)}$	Turn-off delay time			—	—	600	ns
t_f	Turn-off fall time			—	—	350	ns
t_{rr} (Note 1)	Reverse recovery time			—	—	250	ns
Q_{rr} (Note 1)	Reverse recovery charge			—	13	—	μC
V_{EC}(Note 1)	Emitter-collector voltage	I_E = 300A, V_{GE} = 0V		—	—	3.2	V
$R_{th(j-c)Q}$	Thermal resistance*1	IGBT part (1/2 module)		—	—	0.11	°C/W
$R_{th(j-c)R}$		FWDi part (1/2 module)		—	—	0.18	°C/W
$R_{th(c-f)}$	Contact thermal resistance	Case to fin, Thermal compound Applied*2 (1/2 module)		—	0.02	—	°C/W
$R_{th(j-c')Q}$	Thermal resistance	Tc measured point is just under the chips		—	—	0.046*3	°C/W
R_G	External gate resistance			1.0	—	10	Ω

*1 : Tc measured point is shown in page OUTLINE DRAWING.
*2 : Typical value is measured by using Shin-etsu Silicone "G-746".
*3 : Tc' measured point is just under the chips.
If you use this value, $R_{th(f-a)}$ should be measured just under the chips.

Note 1. I_E, V_{EC}, t_{rr} & Q_{rr} represent characteristics of the anti-parallel, emitter to collector free-wheel diode (FWDi).
2. Pulse width and repetition rate should be such that the device junction temp. (T_j) does not exceed T_{jmax} rating.
3. Junction temperature (T_j) should not increase beyond 150°C.